Quad 2-Input “NAND” Schmitt Trigger

MC14093B

The MC14093B Schmitt trigger is constructed with MOS P-channel and N-channel enhancement mode devices in a single monolithic structure. These devices find primary use where low power dissipation and/or high noise immunity is desired. The MC14093B may be used in place of the MC14011B quad 2-input NAND gate for enhanced noise immunity or to “square up” slowly changing waveforms.

Features

- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- Capable of Driving Two Low-Power TTL Loads or One Low-Power Schottky TTL Load Over the Rated Temperature Range
- Triple Diode Protection on All Inputs
- Pin-for-Pin Compatible with CD4093
- Can be Used to Replace MC14011B
- Independent Schmitt-Trigger at each Input
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS (Voltages Referenced to V_{SS})

Symbol	Parameter	Value	Unit
V_{DD}	DC Supply Voltage Range	−0.5 to +18.0	V
V_{in}, V_{out}	Input or Output Voltage Range (DC or Transient)	−0.5 to V_{DD} + 0.5	V
I_{in}, I_{out}	Input or Output Current (DC or Transient) per Pin	±10	mA
P_D	Power Dissipation, per Package (Note 1)	500	mW
T_A	Ambient Temperature Range	−55 to +125	°C
T_{stg}	Storage Temperature Range	−65 to +150	°C
T_L	Lead Temperature (8-Second Soldering)	260	°C

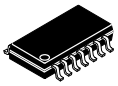
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Temperature Derating: “D/DW” Packages: –7.0 mW/°C From 65 °C To 125 °C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $V_{SS} \le (V_{in}$ or $V_{out}) \le V_{DD}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.

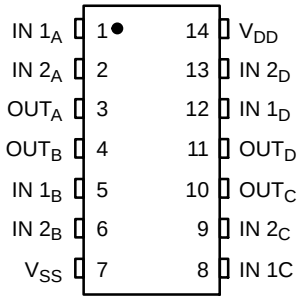
SOIC-14
D SUFFIX
CASE 751A



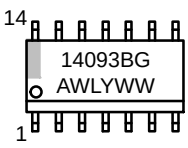
SOEIAJ-14
F SUFFIX
CASE 965

TSSOP-14
DT SUFFIX
CASE 948G

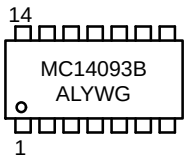
PIN ASSIGNMENT



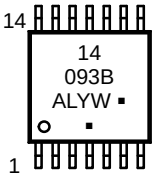
MARKING DIAGRAMS



SOIC-14



SOEIAJ-14



TSSOP-14

A	= Assembly Location
WL, L	= Wafer Lot
YY, Y	= Year
WW, W	= Work Week
G or ▪	= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 2.

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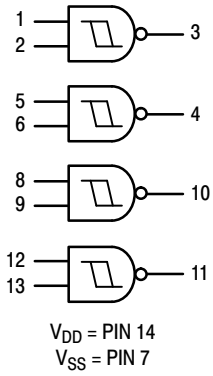
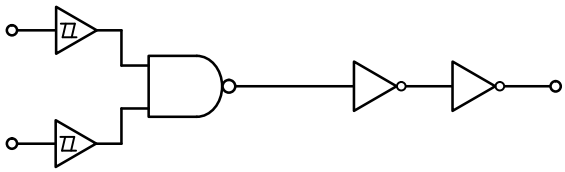
LOGIC DIAGRAM



V_{DD} = PIN 14
V_{SS} = PIN 7

EQUIVALENT CIRCUIT SCHEMATIC

(1/4 OF CIRCUIT SHOWN)



ORDERING INFORMATION

Device	Package	Shipping†
MC14093BDG	SOIC-14 (Pb-Free)	55 Units / Rail
MC14093BDR2G	SOIC-14 (Pb-Free)	2500 Units / Tape & Reel
NLV14093BDR2G*	SOIC-14 (Pb-Free)	2500 Units / Tape & Reel
MC14093BDTR2G	TSSOP-14 (Pb-Free)	2500 Units / Tape & Reel
NLV14093BDTR2G*	TSSOP-14 (Pb-Free)	2500 Units / Tape & Reel

DISCONTINUED (Note 2)

NLV14093BDG*	SOIC-14 (Pb-Free)	55 Units / Rail
MC14093BFELG	SOEIAJ-14 (Pb-Free)	2000 Units / Tape & Reel

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

* NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

2. **DISCONTINUED:** These devices are not recommended for new design. Please contact your **onsemi** representative for information. The most current information on these devices may be available on www.onsemi.com.

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ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

Characteristic	Symbol	V_{DD} Vdc	−55 °C Min	−55 °C Max	25 °C Min	25 °C Typ (Note 3)	25 °C Max	125 °C Min	125 °C Max	Unit
Output Voltage “0” Level V_{in} = V_{DD} or 0	V_{OL}	5.0 10 15	– – –	0.05 0.05 0.05	– – –	0 0 0	0.05 0.05 0.05	– – –	0.05 0.05 0.05	Vdc
“1” Level V_{in} = 0 or V_{DD}	V_{OH}	5.0 10 15	4.95 9.95 14.95	– – –	4.95 9.95 14.95	5.0 10 15	– – –	4.95 9.95 14.95	– – –	Vdc
Output Drive Current	I_{OH}									mAdc
(V_{OH} = 2.5 Vdc) Source		5.0	–3.0	–	–2.4	–4.2	–	–1.7	–	
(V_{OH} = 4.6 Vdc)		5.0	–0.64	–	–0.51	–0.88	–	–0.36	–	
(V_{OH} = 9.5 Vdc)		10	–1.6	–	–1.3	–2.25	–	–0.9	–	
(V_{OH} = 13.5 Vdc)		15	–4.2	–	–3.4	–8.8	–	–2.4	–	
(V_{OL} = 0.4 Vdc) Sink	I_{OL}	5.0	0.64	–	0.51	0.88	–	0.36	–	mAdc
(V_{OL} = 0.5 Vdc)		10	1.6	–	1.3	2.25	–	0.9	–	
(V_{OL} = 1.5 Vdc)		15	4.2	–	3.4	8.8	–	2.4	–	
Input Current	I_{in}	15	–	±0.1	–	±0.00001	±0.1	–	±1.0	μAdc
Input Capacitance (V_{in} = 0)	C_{in}	–	–	–	–	5.0	7.5	–	–	pF
Quiescent Current (Per Package)	I_{DD}	5.0 10 15	– – –	0.25 0.5 1.0	– – –	0.0005 0.0010 0.0015	0.25 0.5 1.0	– – –	7.5 15 30	μAdc
Total Supply Current (Notes 4 & 5) (Dynamic plus Quiescent, Per Package) (C_L = 50 pF on all outputs, all buffers switching)	I_T	5.0 10 15	I_T = (1.2 μA/kHz) f + I_{DD} I_T = (2.4 μA/kHz) f + I_{DD} I_T = (3.6 μA/kHz) f + I_{DD}							μAdc
Hysteresis Voltage	V_H†	5.0 10 15	0.3 1.2 1.6	2.0 3.4 5.0	0.3 1.2 1.6	1.1 1.7 2.1	2.0 3.4 5.0	0.3 1.2 1.6	2.0 3.4 5.0	Vdc
Threshold Voltage Positive-Going	V_{T+}	5.0 10 15	2.2 4.6 6.8	3.6 7.1 10.8	2.2 4.6 6.8	2.9 5.9 8.8	3.6 7.1 10.8	2.2 4.6 6.8	3.6 7.1 10.8	Vdc
Negative-Going	V_{T-}	5.0 10 15	0.9 2.5 4.0	2.8 5.2 7.4	0.9 2.5 4.0	1.9 3.9 5.8	2.8 5.2 7.4	0.9 2.5 4.0	2.8 5.2 7.4	Vdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Data labelled “Typ” is not to be used for design purposes but is intended as an indication of the IC’s potential performance.
4. The formulas given are for the typical characteristics only at 25 °C.
5. To calculate total supply current at loads other than 50 pF:

$$I_T(C_L) = I_T(50\ pF) + (C_L - 50)\ Vfk$$

where: I_T is in μA (per package), C_L in pF, V = (V_{DD} − V_{SS}) in volts, f in kHz is input frequency, and k = 0.004.

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SWITCHING CHARACTERISTICS (C_L = 50 pF, T_A = 25 °C)

Characteristic	Symbol	V_{DD} Vdc	Min	Typ (Note 6)	Max	Unit
Output Rise Time	t_{TLH}	5.0 10 15	– – –	100 50 40	200 100 80	ns
Output Fall Time	t_{THL}	5.0 10 15	– – –	100 50 40	200 100 80	ns
Propagation Delay Time	t_{PLH}, t_{PHL}	5.0 10 15	– – –	125 50 40	250 100 80	ns

6. Data labeled “Typ” is not to be used for design purposes but is intended as an indication of the IC’s potential performance.

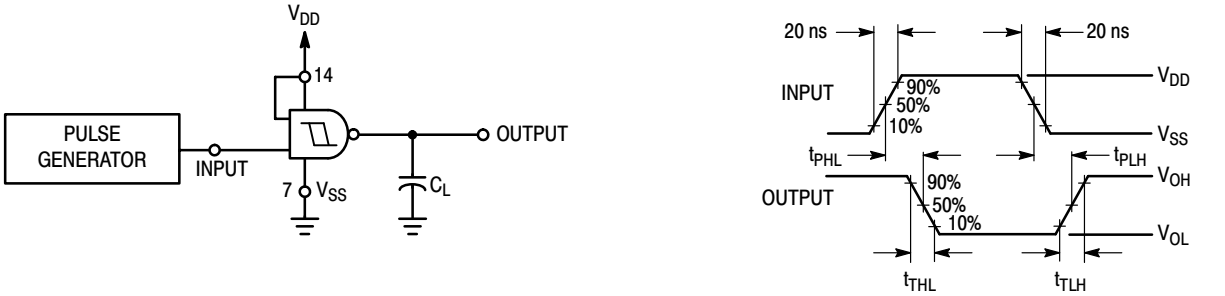
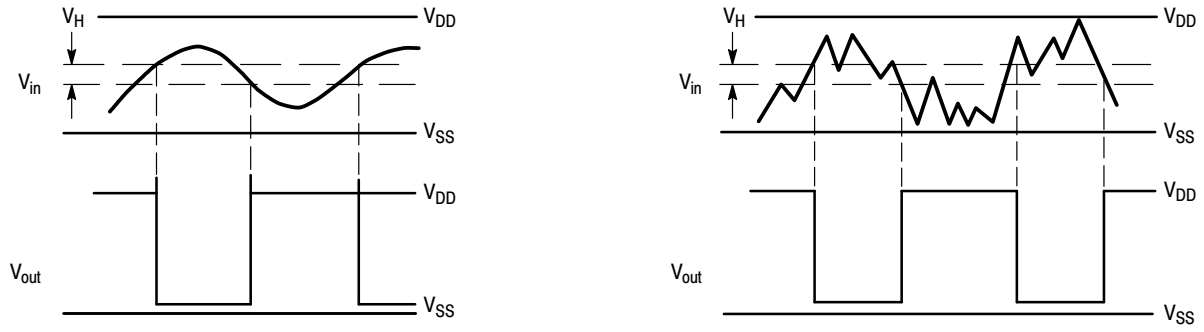


Figure 1. Switching Time Test Circuit and Waveforms



(a) Schmitt Triggers will square up inputs with slow rise and fall times.

(b) A Schmitt trigger offers maximum noise immunity in gate applications.

Figure 2. Typical Schmitt Trigger Applications

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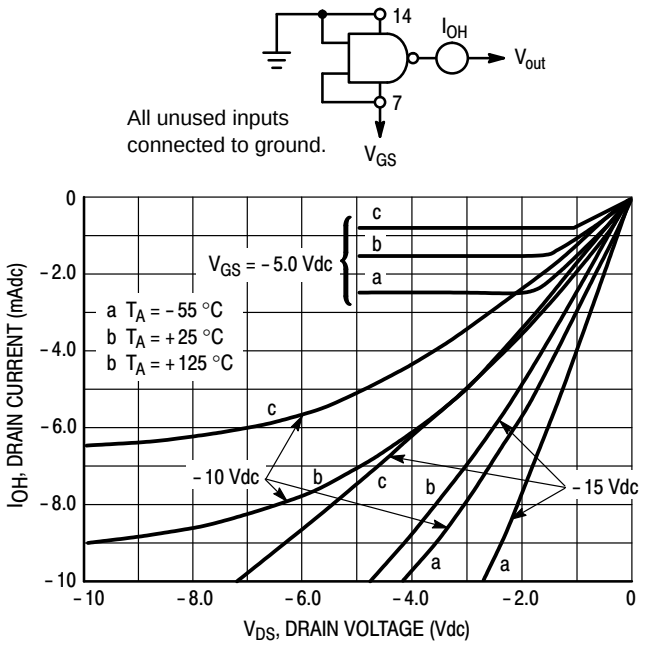

Figure 3. Typical Output Source Characteristics Test Circuit

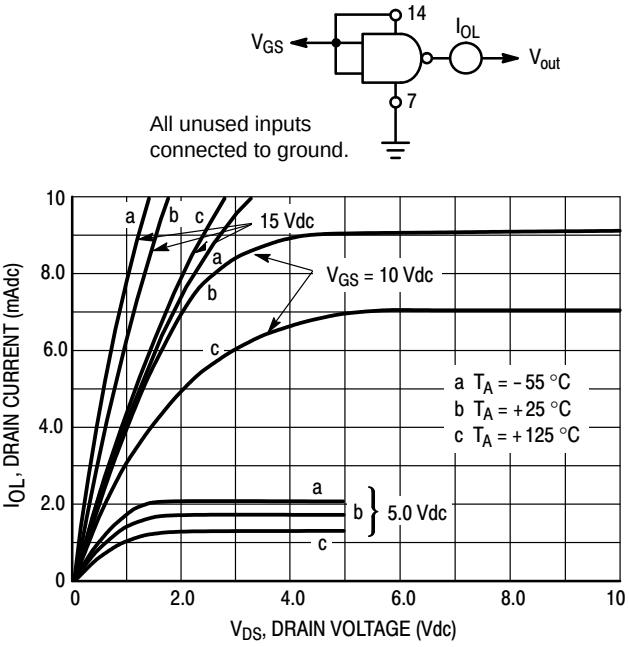

Figure 4. Typical Output Sink Characteristics Test Circuit

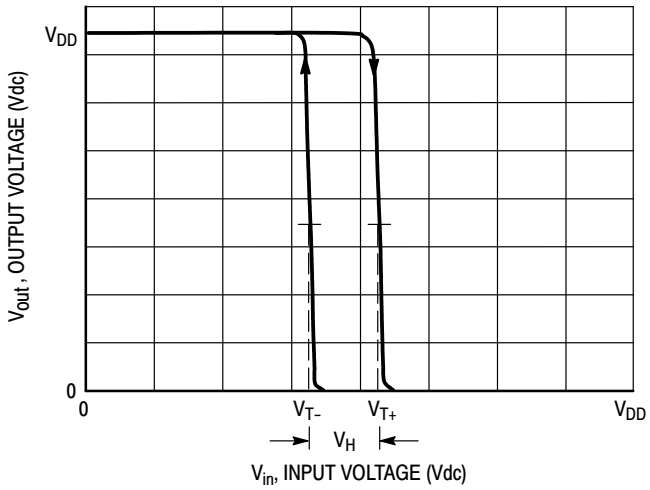

Figure 5. Typical Transfer Characteristics

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REVISION HISTORY

Revision	Description of Changes	Date
11	Rebranded the Data Sheet to **onsemi** format. NLV14093BDG and MC14093BFELG OPNs Marked as Discontinued.	8/27/2025

This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.

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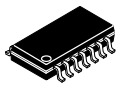
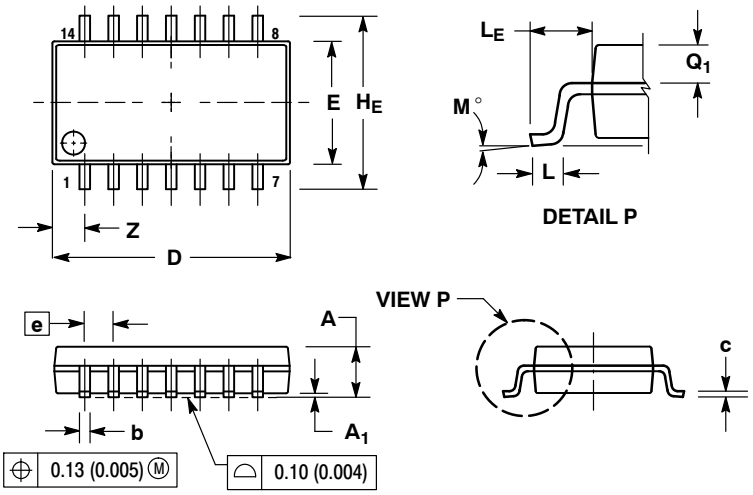
SOEIAJ−14
CASE 965−01
ISSUE B

DATE 29 FEB 2008



SCALE 1:1



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	---	2.05	---	0.081
A_1	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
c	0.10	0.20	0.004	0.008
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
e	1.27 BSC		0.050 BSC	
H_E	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
L_E	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10 °
Q_1	0.70	0.90	0.028	0.035
Z	---	1.42	---	0.056

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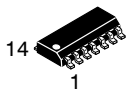

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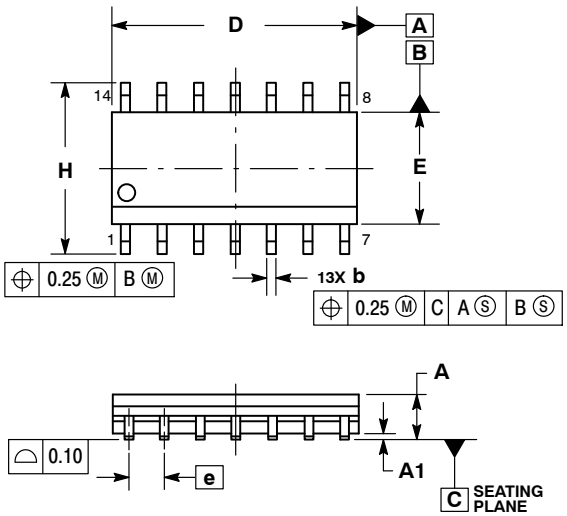
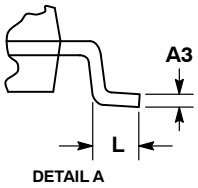
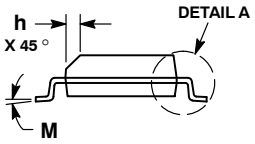
SOIC−14 NB
CASE 751A−03
ISSUE L

DATE 03 FEB 2016



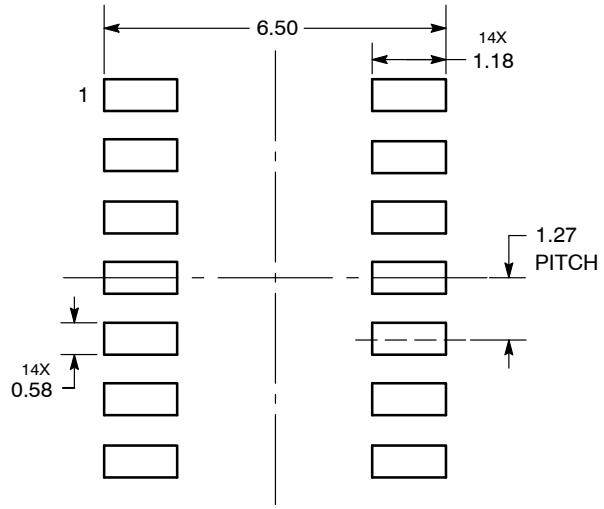




NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
A3	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
M	0 °	7 °	0 °	7 °

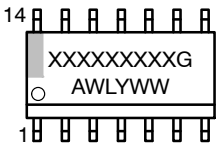
SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code
A = Assembly Location
WL = Wafer Lot
Y = Year
WW = Work Week
G = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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SOIC−14
CASE 751A−03
ISSUE L

DATE 03 FEB 2016

STYLE 1:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. NO CONNECTION
5. ANODE/CATHODE
6. NO CONNECTION
7. ANODE/CATHODE
8. ANODE/CATHODE
9. ANODE/CATHODE
10. NO CONNECTION
11. ANODE/CATHODE
12. ANODE/CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 2:
CANCELLED

STYLE 3:
PIN 1. NO CONNECTION
2. ANODE
3. ANODE
4. NO CONNECTION
5. ANODE
6. NO CONNECTION
7. ANODE
8. ANODE
9. ANODE
10. NO CONNECTION
11. ANODE
12. ANODE
13. NO CONNECTION
14. COMMON CATHODE

STYLE 4:
PIN 1. NO CONNECTION
2. CATHODE
3. CATHODE
4. NO CONNECTION
5. CATHODE
6. NO CONNECTION
7. CATHODE
8. CATHODE
9. CATHODE
10. NO CONNECTION
11. CATHODE
12. CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 5:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. ANODE/CATHODE
5. ANODE/CATHODE
6. NO CONNECTION
7. COMMON ANODE
8. COMMON CATHODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. ANODE/CATHODE
12. ANODE/CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 6:
PIN 1. CATHODE
2. CATHODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE
7. CATHODE
8. ANODE
9. ANODE
10. ANODE
11. ANODE
12. ANODE
13. ANODE
14. ANODE

STYLE 7:
PIN 1. ANODE/CATHODE
2. COMMON ANODE
3. COMMON CATHODE
4. ANODE/CATHODE
5. ANODE/CATHODE
6. ANODE/CATHODE
7. ANODE/CATHODE
8. ANODE/CATHODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. COMMON CATHODE
12. COMMON ANODE
13. ANODE/CATHODE
14. ANODE/CATHODE

STYLE 8:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. NO CONNECTION
5. ANODE/CATHODE
6. ANODE/CATHODE
7. COMMON ANODE
8. COMMON ANODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. NO CONNECTION
12. ANODE/CATHODE
13. ANODE/CATHODE
14. COMMON CATHODE

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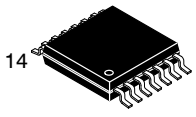
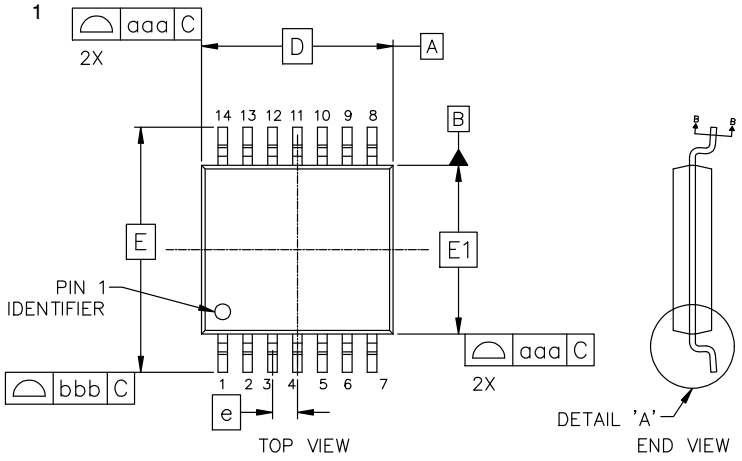
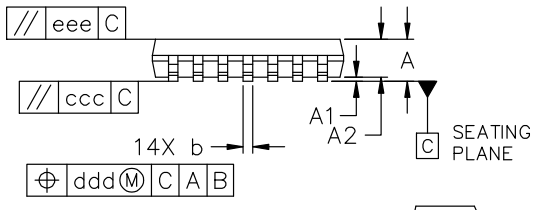
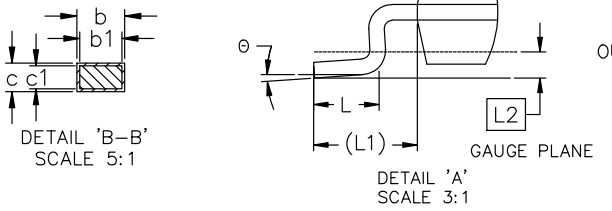


TSSOP−14 5.00x4.40x0.95, 0.65P
CASE 948G
ISSUE D

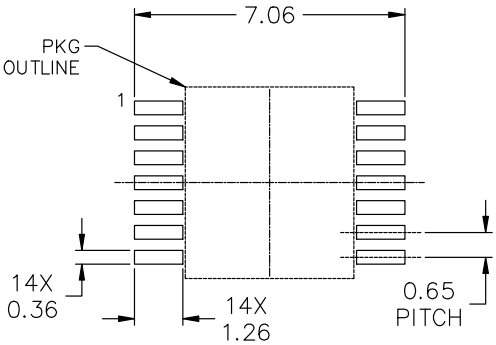
DATE 30 JUN 2026







MILLIMETERS			
DIM	MIN	NOM	MAX
A	−−−	−−−	1.20
A1	0.05	0.10	0.15
A2	0.85	0.95	1.05
b	0.19	0.25	0.30
b1	0.19	0.22	0.25
c	0.09	0.15	0.20
c1	0.09	0.12	0.16
D	5.00 BSC		
E	6.40 BSC		
E1	4.40 BSC		
e	0.65 BSC		
L	0.50	0.63	0.75
L1	1.00 REF		
L2	0.25 BSC		
θ	0°	4°	8°
TOLERANCE FORM & POSITION			
aaa	0.10		
bbb	0.15		
ccc	0.08		
ddd	0.10		
eee	0.10		

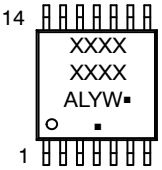


RECOMMENDED MOUNTING FOOTPRINT

*For additional information on our Pb−Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NOTES:
1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D DOES NOT INCLIDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE.
4. DIMENSION E1 DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 PER SIDE.
5. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF THE b DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

GENERIC MARKING DIAGRAM*



A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb−Free Package
(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	TSSOP−14 5.00x4.40x0.95, 0.65P	PAGE 1 OF 1

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